

QRD1113, QRD1114 Reflective Object Sensor

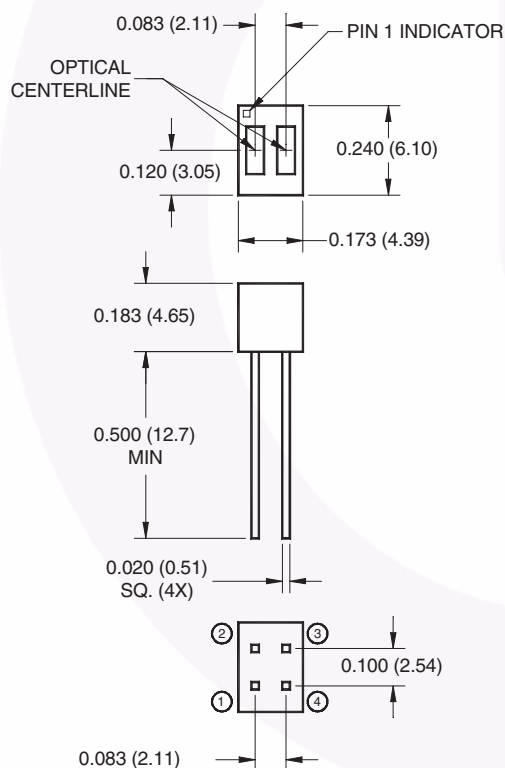
Features

- Phototransistor Output
- No contact surface sensing
- Unfocused for sensing diffused surfaces
- Compact Package
- Daylight filter on sensor

Description

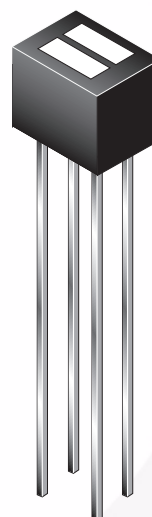
The QRD1113/14 reflective sensor consists of an infra-red emitting diode and an NPN silicon phototransistor mounted side by side in a black plastic housing. The on-axis radiation of the emitter and the on-axis response of the detector are both perpendicular to the face of the QRD1113/14. The phototransistor responds to radiation emitted from the diode only when a reflective object or surface is in the field of view of the detector.

Package Dimensions

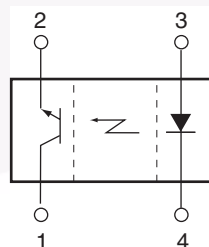


PIN 1 COLLECTOR
PIN 2 EMITTER

PIN 3 ANODE
PIN 4 CATHODE



Schematic



Notes:

1. Dimensions for all drawings are in inches (millimeters).
2. Tolerance of $\pm .010$ (.25) on all non-nominal dimensions unless otherwise specified.
3. Pins 2 and 4 typically .050" shorter than pins 1 and 3.
4. Dimensions controlled at housing surface.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Rating	Units
T_{OPR}	Operating Temperature	-40 to +85	$^\circ\text{C}$
T_{STG}	Storage Temperature	-40 to +100	$^\circ\text{C}$
$T_{\text{SOL-I}}$	Lead Temperature (Solder Iron) ^(2,3)	240 for 5 sec	$^\circ\text{C}$
$T_{\text{SOL-F}}$	Lead Temperature (Solder Flow) ^(2,3)	260 for 10 sec	$^\circ\text{C}$
EMITTER			
I_F	Continuous Forward Current	50	mA
V_R	Reverse Voltage	5	V
P_D	Power Dissipation ⁽¹⁾	100	mW
SENSOR			
V_{CEO}	Collector-Emitter Voltage	30	V
V_{ECO}	Emitter-Collector Voltage		V
P_D	Power Dissipation ⁽¹⁾	100	mW

Electrical/Optical Characteristics ($T_A = 25^\circ\text{C}$)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
INPUT (Emitter)						
V_F	Forward Voltage	$I_F = 20\text{mA}$			1.7	V
I_R	Reverse Leakage Current	$V_R = 5\text{V}$			100	μA
λ_{PE}	Peak Emission Wavelength	$I_F = 20\text{mA}$		940		nm
OUTPUT (Sensor)						
BV_{CEO}	Collector-Emitter Breakdown	$I_C = 1\text{mA}$	30			V
BV_{ECO}	Emitter-Collector Breakdown	$I_E = 0.1\text{mA}$	5			V
I_D	Dark Current	$V_{\text{CE}} = 10\text{V}, I_F = 0\text{mA}$			100	nA
COUPLED						
$I_{\text{C(ON)}}$	QRD1113 Collector Current	$I_F = 20\text{mA}, V_{\text{CE}} = 5\text{V}, D = .050''^{(6,8)}$	0.300			mA
$I_{\text{C(ON)}}$	QRD1114 Collector Current	$I_F = 20\text{mA}, V_{\text{CE}} = 5\text{V}, D = .050''^{(6,8)}$	1			mA
$V_{\text{CE(SAT)}}$	Collector Emitter Saturation Voltage	$I_F = 40\text{mA}, I_C = 100\mu\text{A}, D = .050''^{(6,8)}$			0.4	V
I_{CX}	Cross Talk	$I_F = 20\text{mA}, V_{\text{CE}} = 5\text{V}, E_E = 0^{(7)}$		.200	10	μA
t_r	Rise Time	$V_{\text{CE}} = 5\text{V}, R_L = 100\Omega, I_{\text{C(ON)}} = 5\text{mA}$		10		μs
t_f	Fall Time			50		μs

Notes:

1. Derate power dissipation linearly 1.33mW/ $^\circ\text{C}$ above 25°C .
2. RMA flux is recommended.
3. Methanol or isopropyl alcohols are recommended as cleaning agents.
4. Soldering iron tip 1/16" (1.6 mm) minimum from housing.
5. As long as leads are not under any stress or spring tension.
6. D is the distance from the sensor face to the reflective surface.
7. Crosstalk (I_{CX}) is the collector current measured with the indicated current on the input diode and with no reflective surface.
8. Measured using Eastman Kodak neutral white test card with 90% diffused reflecting as a reflecting surface.

Typical Performance Curves

Fig. 1 Forward Voltage vs. Forward Current

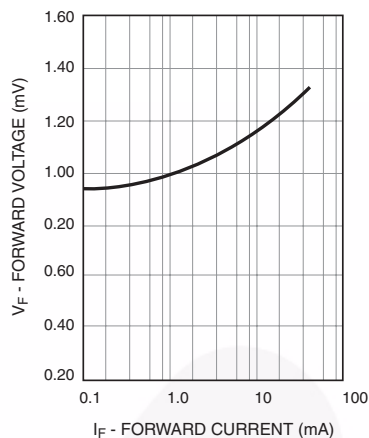


Fig. 2 Normalized Collector Current vs. Forward Current

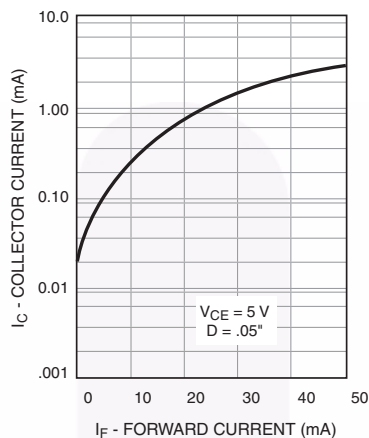


Fig. 3 Normalized Collector Current vs. Temperature

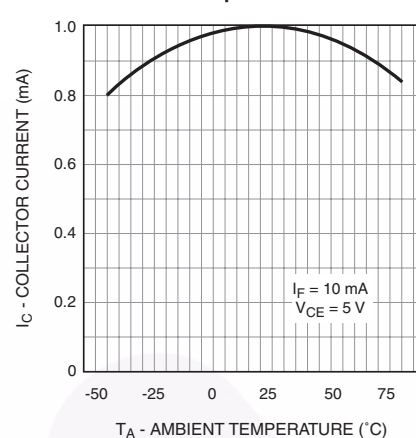


Fig. 4 Normalized Collector Dark Current vs. Temperature

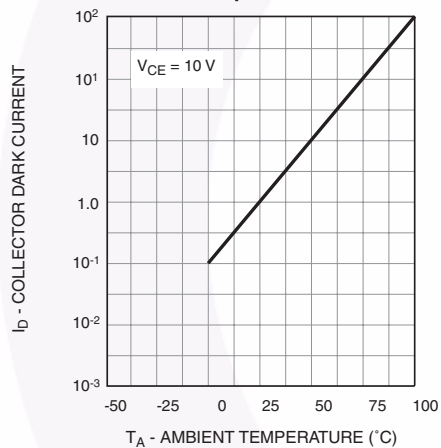
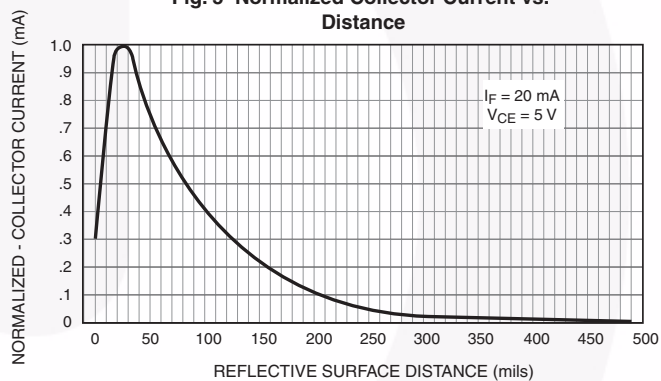


Fig. 5 Normalized Collector Current vs. Distance





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